NSN 5961-01-514-2180

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Inclosure Material:

Metal

Overall Length:

0.975 inches

Overall Height:

0.200 inches

Overall Width:

0.670 inches

Mounting Facility Quantity:

2

Mounting Method:

Slot

Features Provided:

Low noise

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

70.0 drain to gate voltage and 70.0 drain to source voltage and 30.0 gate to source voltage

Current Rating Per Characteristic:

4.00 amperes source cutoff current of standard range

Power Rating Per Characteristic:

100.0 watts small-signal input power, common-collector absolute

Product Name:

Silicon rf power, vdmos transistor

Special Features:

8gold metalized; package style - ak; high efficiency; linear; high gain; junction temperature plus 200.0 degrees c; storage temperature minus 65.0 to plus 150.0 degrees c; designed specifically for broadband radio frequency (rf) applications

Terminal Type And Quantity:

2 tab, solder lug

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

Fiig:

A110a0